

In re Patent Application of:  
**CROCE ET AL.**  
Serial No. 09/839,596  
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TABLE 2

region	Dopant	Thickness [ $\mu\text{m}$ ]	Doping [Atoms $\text{cm}^{-3}$ ]
n-body (conductivity "N")	phosphorous	0.25-0.75	$5 \times 10^{17}$ - $5 \times 10^{18}$
body-buffer (conductivity "P")	boron	0.15-0.45 below junction with n- body	$5 \times 10^{16}$ - $5 \times 10^{17}$
drain well region (conductivity "P")	boron	1.5-4.5 below junction with body- buffer	$2.5 \times 10^{15}$ - $2.5 \times 10^{16}$

In the Claims:

Please amend Claims 5 and 14 as follows:

5. (Amended) A lateral diffused metal oxide semiconductor (LDMOS) integrated device comprising:

a semiconductor substrate;

a drain region of a first conductivity type adjacent said semiconductor substrate and comprising a superficial buffer region being more heavily doped than adjacent portions of said drain region;

a body region surrounded by said buffer region and having a second conductivity type; and

a source region in said body region and having the first conductivity type.

14. (Amended) A lateral diffused metal oxide semiconductor (LDMOS) integrated device comprising: